ABSTRACT OF THE DISCLOSURE

A silicon-on-isolator CMOS integrated circuit device includes a semiconductor substrate, an isolation layer formed over the semiconductor substrate, an n-type MOS transistor having a gate, a drain region, and a source region formed over the isolation layer, and a p-type MOS transistor having a gate, a drain region, and a source region formed over the isolation layer and contiguous with the n-type MOS transistor, wherein the n-type MOS transistor and the p-type MOS transistor form a silicon controlled rectifier to provide electrostatic discharge protection.

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